







**TXS0104V** SCES964 - JUNE 2024

# TXS0104V 4-Bit Bi-directional, Level-Shifting, Voltage Translator for Open-Drain and **Push-Pull Applications**

#### 1 Features

- No direction-control signal needed
- Maximum data rates:
  - 24Mbps (push pull)
  - 2Mbps (open drain)
- 1.65V to 3.6V on A port and 2.3V to 5.5V on B port  $(V_{CCA} \leq V_{CCB})$
- No power-supply sequencing required V<sub>CCA</sub> or V<sub>CCB</sub> can be ramped first
- Latch-up performance exceeds 100mA per JESD 78, class II
- ESD protection exceeds JESD 22:
  - A port:
    - 2000V Human-Body Model (A114-B)
    - 500V Charged-Device Model (C101)
  - B port:
    - 5000V Human-Body Model (A114-B)
    - 500V Charged-Device Model (C101)

# 2 Applications

- Handset
- **Smartphone**
- **Tablet**
- **Desktop PC**

## 3 Description

This 4-bit non-inverting translator uses two separate configurable power-supply rails. The A port is designed to track V<sub>CCA</sub>. V<sub>CCA</sub> accepts any supply voltage from 1.65V to 3.6V. V<sub>CCA</sub> must be less than or equal to V<sub>CCB</sub>. The B port is designed to track V<sub>CCB</sub>. V<sub>CCB</sub> accepts any supply voltage from 2.3V to 5.5V. This allows for low-voltage bidirectional translation between any of the 1.8V, 2.5V, 3.3V, and 5V voltage nodes.

When the output-enable (OE) input is low, all outputs are placed in the high-impedance state.

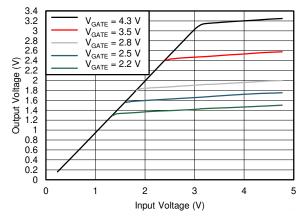
The TXS0104V is designed so that the OE input circuit is supplied by V<sub>CCA</sub>.

For the high-impedance state during power up or power down, tie OE to GND through a pull-down resistor; the current-sourcing capability of the driver determines the minimum value of the resistor.

Package Information

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
	PW (TSSOP, 14)	5mm × 6.4mm
	BQA (WQFN, 12)	3mm × 2.5mm
TXS0104V	RUT (UQFN, 12)	2mm × 1.7mm
	RGY (VQFN, 14)	3.5mm × 3.5mm
	D (SOIC, 14)	8.65mm × 6mm

- For more information, see Section 11. (1)
- The package size (length × width) is a nominal value and includes pins, where applicable.



Transfer Characteristics of an N-Channel Transistor

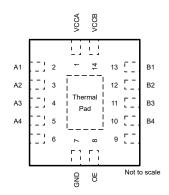


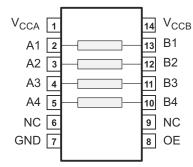
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# 4 Pin Configuration and Functions



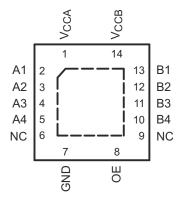


NC - No internal connection

Figure 4-2. D and PW Package, 14-Pin SOIC and TSSOP (Top View)

NC - No internal connection

Figure 4-1. BQA Package, 14-Pin WQFN (Top View)



NC - No internal connection

PIN

Figure 4-3. RGY Package, 14-Pin VQFN (Top View)

Table 4-1. Pin Functions: BQA, PW, D, or RGY

TYPE(1) **DESCRIPTION** NAME NO. Α1 2 I/O Input/output A1. Referenced to V<sub>CCA</sub>. A2 Input/output A2. Referenced to V<sub>CCA</sub>. 3 I/O А3 4 I/O Input/output A3. Referenced to V<sub>CCA</sub>. A4 I/O 5 Input/output A4. Referenced to V<sub>CCA</sub>. Input/output B1. Referenced to V<sub>CCB</sub>. В1 13 I/O

B2	12	I/O	Input/output B2. Referenced to V <sub>CCB</sub> .
В3	11	I/O	Input/output B3. Referenced to V <sub>CCB</sub> .
B4	10	I/O	Input/output B4. Referenced to V <sub>CCB</sub> .
GND	7	_	Ground
OE	8	I	3-state output-mode enable. Pull OE low to place all outputs in 3-state mode. Referenced to $V_{\text{CCA}}$ .
V <sub>CCA</sub>	1	_	A-port supply voltage. $1.65V \le V_{CCA} \le 3.6V$ and $V_{CCA} \le V_{CCB}$ .
V <sub>CCB</sub>	14	_	B-port supply voltage. $2.3V \le V_{CCB} \le 5.5V$ .
Thermal Pa	ad	_	For the RGY package, the exposed center thermal pad must be connected to ground

(1) I = input, O = output



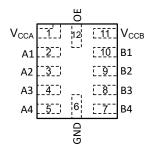


Figure 4-4. RUT Package, 12-Pin UQFN (Transparent Top View)

Table 4-2. Pin Functions: RUT

Р	IN	TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.	ITPE(*)	DESCRIPTION
A1	2	I/O	Input/output A1. Referenced to V <sub>CCA</sub> .
A2	3	I/O	Input/output A2. Referenced to V <sub>CCA</sub> .
A3	4	I/O	Input/output A3. Referenced to V <sub>CCA</sub> .
A4	5	I/O	Input/output A4. Referenced to V <sub>CCA</sub> .
B1	10	I/O	Input/output B1. Referenced to V <sub>CCB</sub> .
B2	9	I/O	Input/output B2. Referenced to V <sub>CCB</sub> .
В3	8	I/O	Input/output B3. Referenced to V <sub>CCB</sub> .
B4	7	I/O	Input/output B4. Referenced to V <sub>CCB</sub> .
GND	6	_	Ground
OE	12	I	3-state output-mode enable. Pull OE low to place all outputs in 3-state mode. Referenced to $V_{\text{CCA}}$ .
V <sub>CCA</sub>	1	_	A-port supply voltage. $1.65 \text{V} \le \text{V}_{\text{CCA}} \le 3.6 \text{V}$ and $\text{V}_{\text{CCA}} \le \text{V}_{\text{CCB}}$ .
V <sub>CCB</sub>	11	_	B-port supply voltage. $2.3V \le V_{CCB} \le 5.5V$ .

<sup>(1)</sup> I = input, O = output



# 5 Specifications

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CCA</sub>	Supply voltage A		-0.5	4.6	V
V <sub>CCB</sub>	Supply voltage B		-0.5	6.5	V
		I/O Ports (A Port)	-0.5	4.6	
V <sub>I</sub>	Input Voltage <sup>(2)</sup>	I/O Ports (B Port)	-0.5	6.5	V
		OE	-0.5	4.6	
V	V-14	A Port	-0.5	4.6	V
Vo	Voltage applied to any output in the high-impedance or power-off state <sup>(2)</sup>	B Port	-0.5	6.5	, v
V	V-16	A Port	-0.5	V <sub>CCA</sub> + 0.5	
Vo	Voltage applied to any output in the high or low state <sup>(2) (3)</sup>	B Port	-0.5	V <sub>CCB</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
Io	Continuous output current		-50	50	mA
	Continuous current through V <sub>CC</sub> or GND		-100	100	mA
Tj	Junction Temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

- (1) Operation outside the *Absolute Maximum Rating* may cause permanent device damage. *Absolute Maximum Rating* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Condition*. If used outside the *Recommended Operating Condition* but within the *Absolute Maximum Rating*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The output positive-voltage rating may be exceeded up to 6.5V maximum if the output current rating is observed.

### 5.2 ESD Ratings

				VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	A Port	±2000	
\ <u></u>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC 33-00 TV	B Port	±5000	\/
V <sub>(ESD)</sub>	Electrostatic discharge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	A Port	±500	V
		Charged device model (CDIVI), per ANSI/ESDA/JEDEC 35-002	B Port	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

		,	V <sub>CCA</sub>	V <sub>CCB</sub>	MIN	MAX	UNIT
V <sub>CCA</sub>	Supply voltage A			•	1.65	3.6	V
V <sub>CCB</sub>	Supply voltage B				2.3	5.5	V
		A-port I/O's	1.65V to 1.95V	2.3V to 5.5V	V <sub>CCI</sub> - 0.2	V <sub>CCI</sub>	
	High-level input voltage	A-port 1/O's	2.3V to 3.6V	2.3V to 5.5V	V <sub>CCI</sub> - 0.4	V <sub>CCI</sub>	V
V <sub>IH</sub>	I lightever input voltage	B-port I/O's	1.65V to 3.6V	2.3V to 5.5V	V <sub>CCI</sub> - 0.4	V <sub>CCI</sub>	
		OE Input	1.65V to 3.6V	2.3V to 5.5V	V <sub>CCA</sub> x 0.65	5.5	
		A-port I/O's	1.65V to 3.6V	2.3V to 5.5V		0.2	
V <sub>IL</sub>	Low-level input voltage	B-port I/O's	1.65V to 3.6V	2.3V to 5.5V		0.2	V
		OE Input	1.65V to 3.6V	2.3V to 5.5V		V <sub>CCA</sub> x 0.35	
Δt/Δν	Input transition rise and fall time	Push-Pull Driving	1.65V to 3.6V	2.3V to 5.5V		10	ns/V
T <sub>A</sub>	Operating free-air temperature	•			-40	85	°C

- (1) V<sub>CCI</sub> is the V<sub>CC</sub> associated with the input port.
- V<sub>CCO</sub> is the V<sub>CC</sub> associated with the output port.



All control inputs and data I/Os of this device have weak pulldowns to ensure the line is not floating when undefined external to the device. The input leakage from these weak pulldowns is defined by the I<sub>I</sub> specification indicated under Electrical Characteristics.

# 5.4 Thermal Information (PW, RGY, BQA, RUT, D)

				TXS0104V			
	THERMAL METRIC(1)	PW (TSSOP)	RGY (VQFN)	BQA (WQFN)	RUT (UQFN)	D (SOIC)	UNIT
		14 PINS	14 PINS	14 PINS	12 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	115.2	52.9	73.5	150.4	93.7	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	46.2	54.3	76.9	68.6	53.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	70.9	28.4	43.0	76.3	52.0	°C/W
Y <sub>JT</sub>	Junction-to-top characterization parameter	3.4	2.7	4.7	2.4	13.4	°C/W
Y <sub>JB</sub>	Junction-to-board characterization parameter	70.2	28.3	42.9	76.2	51.6	°C/W
R <sub>θ</sub> JC(bottom)	Junction-to-case (bottom) thermal resistance	N/A	12.0	19.6	N/A	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

#### 5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)(1) (2)

					0	perating	free-aiı	temperati	ure (T <sub>A</sub> )		
	PARAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>		25°C		-40°	C to 85°	С	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>OHA</sub>	Port A output high voltage (3)	I <sub>OH</sub> = -20μA	1.65V to 3.6V	2.3V to 5.5V	V <sub>CCA</sub> x 0.8			V <sub>CCA</sub> x 0.8			V
V <sub>OLA</sub>	Low-level output voltage (4)	I <sub>OL</sub> = 1mA	1.65V to 3.6V	2.3V to 5.5V			0.4			0.4	V
V <sub>OHB</sub>	Port B output high voltage	I <sub>OH</sub> = -20μA	1.65V to 3.6V	2.3V to 5.5V	V <sub>CCB</sub> x 0.8			V <sub>CCB</sub> x 0.8			V
V <sub>OLB</sub>	Low-level output voltage (4)	I <sub>OL</sub> = 1mA	1.65V to 3.6V	2.3V to 5.5V			0.4			0.4	V
I	Input leakage current	OE V <sub>I</sub> = V <sub>CC</sub> or GND	1.65V to 3.6V	2.3V to 5.5V	-2		2	-10		10	μA
I <sub>OZ</sub>	Tri-state output current	A or B Port: $V_I = V_{CCI}$ or GND $V_O = V_{CCO}$ or GND OE = GND	1.65V to 3.6V	2.3V to 5.5V	-1		1	-10		10	μA
			1.65V to V <sub>CCB</sub>	2.3V to 5.5V			2.4			3.3	
I <sub>CCA</sub>	V <sub>CCA</sub> supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	0V	5.5V	-3			-3			μA
	Current	10 - 0	3.6V	0V			2.2			2.2	
			1.65V to V <sub>CCB</sub>	2.3V to 5.5V			12			12	
I <sub>CCB</sub>	V <sub>CCB</sub> supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	0V	5.5V			5			5	μA
	Garrent	10 - 0	3.6V	0V	-1			-1			
I <sub>CCA</sub> + I <sub>CCB</sub>	Combined supply current	V <sub>I</sub> = V <sub>CCI</sub> or GND I <sub>O</sub> = 0	1.65V to V <sub>CCB</sub>	2.3V to 5.5V			15			15	μA
C <sub>i</sub>	Control Input Capacitance	V <sub>I</sub> = 3.3V or GND	3.3V	3.3V			6			6	pF
C <sub>io</sub>	Data I/O Capacitance	A or B Port	3.3V	3.3V		5	6.5		12	16.5	pF

<sup>(1)</sup> 

 $V_{CCI}$  is the  $V_{CC}$  associated with the input port  $V_{CCO}$  is the  $V_{CC}$  associated with the output port (2)

Tested at  $V_I = V_{T+(MAX)}$ (3)



(4) Tested at V<sub>I</sub> = V<sub>T-(MIN)</sub>

# 5.6 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15V$

over operating free-air temperature range (unless otherwise noted)

							B-l	Port Sup	ply Volta	age (V <sub>C</sub>	ов)			
	PARAMETER	FROM	то	Test Conditions	2	.5 ± 0.2V	'	3	.3 ± 0.3V	,	5	.0 ± 0.5V	'	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Push-Pull		4			4			5		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)		В	Open-Drain		8.8			9.6			10		ns
t <sub>PLH</sub>	Propagation Delay (Low-to-High)	A	В	Push-Pull		6			6			6		ns
t <sub>PLH</sub>	Propagation Delay (Low-to-High)			Open-Drain		200			160			120		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Push-Pull		4			4		4			ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Open-Drain	5.3		4.4			4.1			ns	
t <sub>PLH</sub>	Propagation Delay (Low-to-High)	- B	A	Push-Pull		5			4		4			ns
t <sub>PLH</sub>	Propagation Delay (Low-to-High)			Open-Drain		173		120			90			ns
t <sub>en</sub>	Enable Time	OE	A or B	-40°C to 85°C		200			200			200		ns
t <sub>dis</sub>	Disable Time	OE	A or B	-40°C to 85°C		250			250			250		ns
t <sub>rA</sub>	Ouput Rise Time	В	^	Push-Pull		9			9			7		ns
t <sub>rA</sub>	Ouput Rise Time	В	A	Open-Drain		150			120			80		ns
t <sub>rB</sub>	Ouput Rise Time	_	В	Push-Pull		10			9			7		ns
t <sub>rB</sub>	Ouput Rise Time	A	В	Open-Drain	145			106			58		ns	
t <sub>fA</sub>	Output Fall Time	_		Push-Pull		5			5			5		ns
t <sub>fA</sub>	Output Fall Time	В	A	Open-Drain	6		6				6		ns	
t <sub>fB</sub>	Output Fall Time	1	Б	Push-Pull		7			7			8		ns
t <sub>fB</sub>	Output Fall Time	A	В	Open-Drain		13			16			16		ns

# 5.7 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2V$

over operating free-air temperature range (unless otherwise noted)

		B-Port Supply Voltage (V <sub>CCB</sub> )												
	PARAMETER	FROM	то	Test Conditions	2.5 ± 0.2V			3	3.3 ± 0.3V	'	5	.0 ± 0.5V	'	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Push-Pull		3			3.4			5		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)		В	Open-Drain		6.3			6			5.8		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)	A	В	Push-Pull		3			4			4		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Open-Drain		200			160			120		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Push-Pull		3			3			4		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)	В	A	Open-Drain		4.7			4.2			4		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Push-Pull	2.1		2.1 2		2			1.9		ns
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Open-Drain		173			120			90		ns
t <sub>en</sub>	Enable Time	OE	A or B	-40°C to 85°C		200			200			200		ns



# 5.7 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2V$ (continued)

over operating free-air temperature range (unless otherwise noted)

							B-l	Port Sup	ply Volt	age (V <sub>C</sub>	св)			
	PARAMETER	FROM	то	Test Conditions	2	.5 ± 0.2V	'	3	3.3 ± 0.3V		5.0 ± 0.5V			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t <sub>dis</sub>	Disable Time	OE	A or B	-40°C to 85°C		250			250			250		ns
t <sub>rA</sub>	Ouput Rise Time	В	^	Push-Pull		7			6			5		ns
t <sub>rA</sub>	Ouput Rise Time	]	Α	Open-Drain		149			101			63		ns
t <sub>rB</sub>	Ouput Rise Time	^	В	Push-Pull		8			7			6		ns
t <sub>rB</sub>	Ouput Rise Time	A		Open-Drain		150			101			63		ns
t <sub>fA</sub>	Output Fall Time	В	^	Push-Pull		5.1			5.2			5		ns
t <sub>fA</sub>	Output Fall Time	]	Α	Open-Drain		6			6			5		ns
t <sub>fB</sub>	Output Fall Time	^	В	Push-Pull		7			6.4			8.7		ns
t <sub>fB</sub>	Output Fall Time	A		Open-Drain		8			9			10		ns

# 5.8 Switching Characteristics, $V_{CCA} = 3.3 \pm 0.3V$

over operating free-air temperature range (unless otherwise noted)

	perating nee-all tempe			,	B-Port Supply Voltage (V <sub>CCB</sub> )							
	PARAMETER	FROM	то	Test Conditions	3	3.3 ± 0.3V		5	.0 ± 0.5V		UNIT	
					MIN	MIN TYP MAX		MIN	MIN TYP MAX			
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Push-Pull		2.4			3.1			
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)	A	В	Open-Drain		4.2			4.6			
t <sub>PLH</sub>	Propagation Delay (Low-to-High)		Б	Push-Pull		4.2			4.4		ns	
t <sub>PLH</sub>	Propagation Delay (Low-to-High)			Open-Drain		160		120				
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)			Push-Pull		2.5		3.3			ns	
t <sub>PHL</sub>	Propagation Delay (Hight-to-Low)	В		Open-Drain		4.5		4			ns	
t <sub>PLH</sub>	Propagation Delay (Low-to-High)	B	A	Push-Pull		2.5			2.6		ns	
t <sub>PLH</sub>	Propagation Delay (Low-to-High)			Open-Drain		139			105		ns	
t <sub>en</sub>	Enable Time	OE	A or B	-40°C to 85°C		200		200			ns	
t <sub>dis</sub>	Disable Time	OE	A or B	-40°C to 85°C		250			250		ns	
t <sub>rA</sub>	Ouput Rise Time	В	Α	Push-Pull		5			4		ns	
t <sub>rA</sub>	Ouput Rise Time	] D	A	Open-Drain		116		85			ns	
t <sub>rB</sub>	Ouput Rise Time	_	В	Push-Pull		6			7		ns	
t <sub>rB</sub>	Ouput Rise Time	A	В	Open-Drain		116		116			ns	
t <sub>fA</sub>	Output Fall Time	В	Α	Push-Pull		8			7.6		ns	
t <sub>fA</sub>	Output Fall Time	]	^	Open-Drain		6		5			ns	
t <sub>fB</sub>	Output Fall Time	_	В	Push-Pull		8.2			10.8		ns	
t <sub>fB</sub>	Output Fall Time	A	D	Open-Drain		7			8			

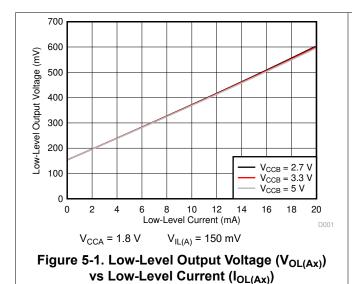


# 5.9 Switching Characteristics: $T_{sk}$ , $T_{MAX}$

over operating free-air temperature range (unless otherwise noted)

			V <sub>CCA</sub>			Operating free-air temperature (T <sub>A</sub> )			
PARAMETER	TEST CON	DITIONS		V <sub>CCB</sub>	-40°	-40°C to 85°C			
					MIN	TYP	MAX		
		Push-Pull Driving	1.8 ± 0.15V	2.5V ± 0.2V			18		
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Push-Pull Driving	1.8 ± 0.15V	3.3V ± 0.3V			21	Mbps	
	one ename enmening	Push-Pull Driving	1.8 ± 0.15V	5V ± 0.5V			23		
		Push-Pull Driving	2.5V ± 0.2V	2.5V ± 0.2V			20		
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Push-Pull Driving	2.5V ± 0.2V	3.3V ± 0.3V			22	Mbps	
raio	One onamer switching	Push-Pull Driving	2.5V ± 0.2V	5V ± 0.5V		24			
TMAX - Maximum Data	50% Duty Cycle Input	Push-Pull Driving	3.3V ± 0.3V	3.3V ± 0.3V			22	Mbps	
Rate	One channel switching	Push-Pull Driving	3.3V ± 0.3V	5V ± 0.5V		24			
		Open-Drain Driving	1.8 ± 0.15V	2.5V ± 0.2V		2 2			
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Open-Drain Driving	1.8 ± 0.15V	3.3V ± 0.3V				Mbps	
T tato		Open-Drain Driving	1.8 ± 0.15V	5V ± 0.5V		2			
		Open-Drain Driving	2.5V ± 0.2V	2.5V ± 0.2V			2		
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Open-Drain Driving	2.5V ± 0.2V	3.3V ± 0.3V		2		Mbps	
T tato		Open-Drain Driving	2.5V ± 0.2V	5V ± 0.5V			2		
TMAX - Maximum Data	50% Duty Cycle Input	Open-Drain Driving	3.3V ± 0.3V	3.3V ± 0.3V			2	N 41	
Rate	One channel switching	Open-Drain Driving	3.3V ± 0.3V	5V ± 0.5V			2	Mbps	
	Push-Pull Driving		1.65V to 3.3V	2.3V to 5.5V	41				
t <sub>w</sub>	Inputs	Open-Drain Driving	1.65V to 3.3V	2.3V to 5.5V	500	500		ns	
	Skew between any two outputs of the same	Push-Pull Driving	1.65V to 3.3V	2.3V to 5.5V			1	ne	
t <sub>sk</sub> - Output skew	package switching in the same direction	Open-Drain Driving	1.65V to 3.3V	2.3V to 5.5V			1	ns	

# **5.10 Typical Characteristics**



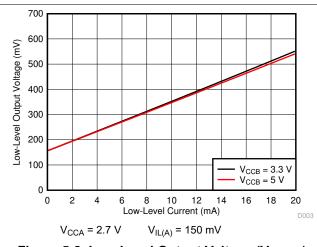
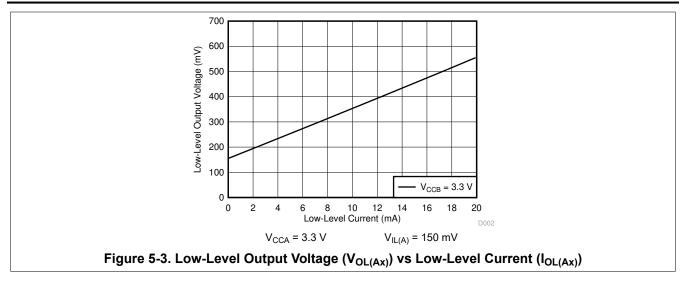


Figure 5-2. Low-Level Output Voltage  $(V_{OL(Ax)})$  vs Low-Level Current  $(I_{OL(Ax)})$ 





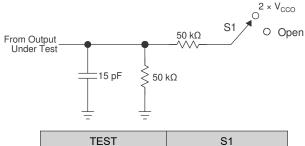
## **6 Parameter Measurement Information**

#### **6.1 Load Circuits**



Figure 6-1. Data Rate, Pulse Duration, Propagation Delay, Output Rise-Time and Fall-Time Propagation Delay, Output Rise-Time and Fall-Time Measurement Using a Push-Pull Driver

Figure 6-2. Data Rate, Pulse Duration, Measurement Using an Open-Drain Driver



TEST	S1
t <sub>PZL</sub> / t <sub>PLZ</sub> (t <sub>dis</sub> )	2 × V <sub>CCO</sub>
t <sub>PHZ</sub> / t <sub>PZH</sub> (t <sub>en</sub> )	Open

Figure 6-3. Load Circuit for Enable-Time and Disable-Time Measurement

- 1.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- 2.  $\,\,t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}.$
- 3.  $V_{\text{CCI}}$  is the  $V_{\text{CC}}$  associated with the input port.
- 4.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port.



# 6.2 Voltage Waveforms

The outputs are measured one at a time, with one transition per measurement. All input pulses are supplied by generators that have the following characteristics:

- PRR ≤ 10MHz
- $Z_O = 50\Omega$
- dv/dt ≥ 1V/ns

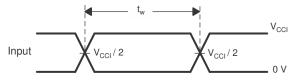


Figure 6-4. Pulse Duration

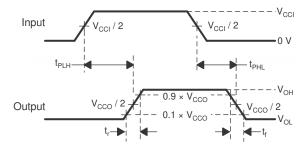
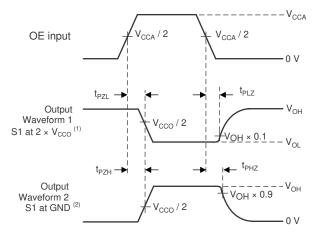


Figure 6-5. Propagation Delay Times



- A. Waveform 1 is for an output with internal such that the output is high, except when OE is high (see Figure 6-3).
- B. Waveform 2 is for an output with conditions such that the output is low, except when OE is high.

Figure 6-6. Enable and Disable Times

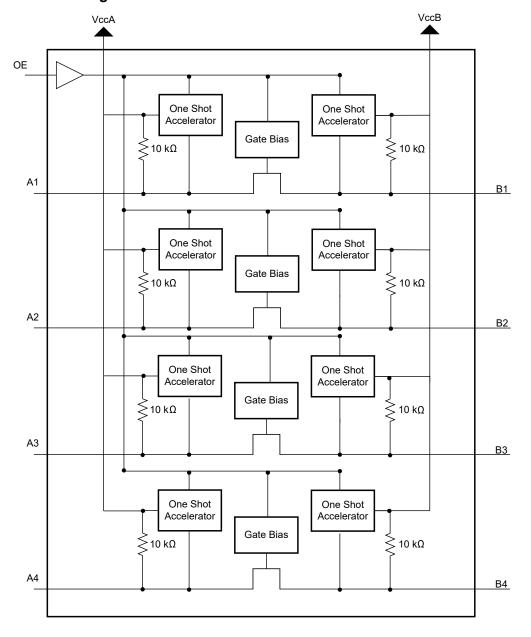


# 7 Detailed Description

#### 7.1 Overview

The TXS0104V device is a directionless voltage-level translator specifically designed for translating logic voltage levels. The A port is able to accept I/O voltages ranging from 1.65V to 3.6V, while the B port can accept I/O voltages from 2.3V to 5.5V. The device is a pass gate architecture with edge rate accelerators (one shots) to improve the overall data rate.  $10k\Omega$  pullup resistors, commonly used in open drain applications, have been conveniently integrated so that an external resistor is not needed. While this device is designed for open drain applications, the device can also translate push-pull CMOS logic outputs.

## 7.2 Functional Block Diagram



#### 7.3 Feature Description

## 7.3.1 Architecture

The TXS0104V architecture (see Figure 7-1) does not require a direction-control signal to control the direction of data flow from A to B or from B to A.

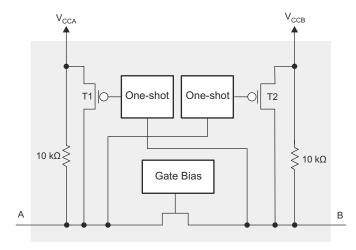


Figure 7-1. Architecture of a TXS0104V Cell

Each A-port I/O has an internal  $10k\Omega$  pullup resistor to  $V_{CCA}$ , and each B-port I/O has an internal  $10k\Omega$  pullup resistor to V<sub>CCB</sub>. The output one-shots detect rising edges on the A or B ports. During a rising edge, the one-shot turns on the PMOS transistors (T1 and T2) for a short duration which speeds up the low-to-high transition.

#### 7.3.2 Input Driver Requirements

The fall time ( $t_{fA}$  and  $t_{fB}$ ) of a signal depends on the output impedance of the external device driving the data I/Os of the TXS0104V device. Similarly, the t<sub>PHL</sub> and maximum data rates also depend on the output impedance of the external driver. The values for tfA, tfB, tPHL, and maximum data rates in the data sheet assume that the output impedance of the external driver is less than  $50\Omega$ .

#### 7.3.3 Power Up

During operation, ensure that  $V_{CCA} \le V_{CCB}$  at all times. During power-up sequencing,  $V_{CCA} \ge V_{CCB}$  does not damage the device, so any power supply can be ramped up first.

#### 7.3.4 Enable and Disable

The TXS0104V device has an OE input that disables the device by setting OE low, which places all I/Os in the high-impedance state. The disable time (t<sub>dis</sub>) indicates the delay between the time when the OE pin goes low and when the outputs actually enter the high-impedance state. The enable time (ten) indicates the amount of time the user must allow for the one-shot circuitry to become operational after the OE pin is taken high.

#### 7.3.5 Pullup and Pulldown Resistors on I/O Lines

Each A-port I/O has an internal  $10k\Omega$  pullup resistor to  $V_{CCA}$ , and each B-port I/O has an internal  $10k\Omega$  pullup resistor to V<sub>CCB</sub>. If a smaller value of pullup resistor is required, an external resistor must be added from the I/O to  $V_{CCA}$  or  $V_{CCB}$  (in parallel with the internal  $10k\Omega$  resistors).

#### 7.4 Device Functional Modes

The TXS0104V device has two functional modes: enabled and disabled. To disable the device set the OE input low, which places all I/Os in a high impedance state. Setting the OE input high will enable the device.

# 8 Application and Implementation

#### **Note**

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

# **8.1 Application Information**

The TXS0104V device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The TXS0104V device is an excellent choice for applications where an open-drain driver is connected to the data I/Os. The TXS0104V device can also be used in applications where a push-pull driver is connected to the data I/Os, but the TXB0104 device might be a better option for such push-pull applications.

## 8.2 Typical Application

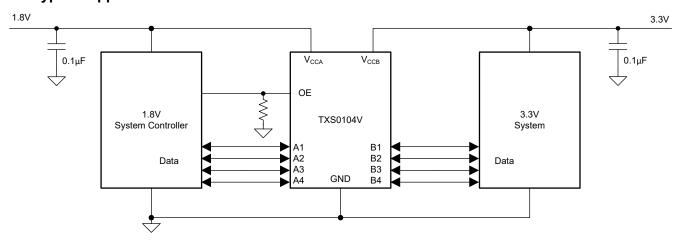


Figure 8-1. Application Schematic

#### 8.2.1 Design Requirements

For this design example, use the parameters listed in Table 8-1.

**Table 8-1. Design Parameters** 

DESIGN PARAMETER	EXAMPLE VALUE			
Input voltage range	1.65 to 3.6V			
Output voltage range	2.3 to 5.5V			

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Product Folder Links: TXS0104V



# 8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
  - Use the supply voltage of the device that is driving the TXS0104V device to determine the input voltage range. For a valid logic high the value must exceed the V<sub>IH</sub> of the input port. For a valid logic low the value must be less than the V<sub>IL</sub> of the input port.
- Output voltage range
  - Use the supply voltage of the device that the TXS0104V device is driving to determine the output voltage range.
  - The TXS0104V device has 10kΩ internal pullup resistors. External pullup resistors can be added to reduce the total RC of a signal trace if necessary.
- An external pull down resistor decreases the output V<sub>OH</sub> and V<sub>OL</sub>. Use Equation 1 to calculate the V<sub>OH</sub> as a
  result of an external pull down resistor.

$$V_{OH} = V_{CCx} \times R_{PD} / (R_{PD} + 10 \, k\Omega) \tag{1}$$

where

 $V_{CCx}$  is the supply voltage on either  $V_{CCA}$  or  $V_{CCB}$   $R_{PD}$  is the value of the external pull down resistor

#### 8.2.3 Application Curve

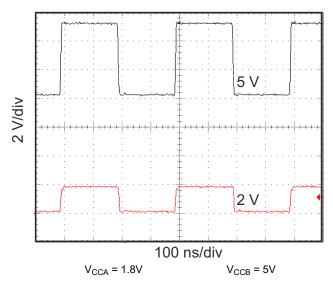


Figure 8-2. Level-Translation of a 2.5MHz Signal

### 8.3 Power Supply Recommendations

The TXS0104V device uses two separate configurable power-supply rails,  $V_{CCA}$  and  $V_{CCB}$ .  $V_{CCB}$  accepts any supply voltage from 2.3V to 5.5V and  $V_{CCA}$  accepts any supply voltage from 1.65V to 3.6V as long as Vs is less than or equal to  $V_{CCB}$ . The A port and B port are designed to track  $V_{CCA}$  and  $V_{CCB}$  respectively allowing for low-voltage bidirectional translation between any of the 1.8V, 2.5V, 3.3V, and 5V voltage nodes.

The TXS0104V device does not require power sequencing between  $V_{CCA}$  and  $V_{CCB}$  during power-up so the power-supply rails can be ramped in any order. A  $V_{CCA}$  value greater than or equal to  $V_{CCB}$  ( $V_{CCA} \ge V_{CCB}$ ) does not damage the device, but during operation,  $V_{CCA}$  must be less than or equal to  $V_{CCB}$  ( $V_{CCA} \le V_{CCB}$ ) at all times.

The output-enable (OE) input circuit is designed so that it is supplied by  $V_{CCA}$  and when the (OE) input is low, all outputs are placed in the high-impedance state. For the high-impedance state of the outputs during power up or power down, the OE input pin must be tied to GND through a pulldown resistor and must not be enabled until  $V_{CCA}$  and  $V_{CCB}$  are fully ramped and stable. The current-sourcing capability of the driver determines the minimum value of the pulldown resistor to ground.

### 8.4 Layout

### 8.4.1 Layout Guidelines

For device reliability, it is recommended to follow common printed-circuit board layout guidelines such as follows:

- Bypass capacitors should be used on power supplies.
- · Short trace lengths should be used to avoid excessive loading.
- PCB signal trace-lengths must be kept short enough so that the round-trip delay of any reflection is less than the one shot duration, approximately 30ns, and encounters low impedance at the source driver.
- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements

#### 8.4.2 Layout Example

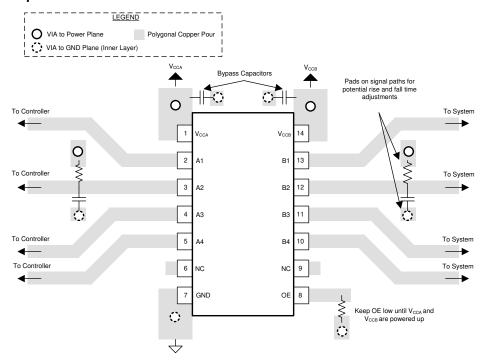


Figure 8-3. TXS0104V Layout Example



# 9 Device and Documentation Support

## 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, Effects of External Pullup and Pulldown Resistors on TXS and TXB Devices application report
- Texas Instruments, Basics of Voltage Translation application report
- Texas Instruments, A Guide to Voltage Translation With TXS-Type Translators application report

### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 9.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

## 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 10 Revision History

DATE	REVISION	NOTES
June 2024	*	Initial Release

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TXS0104VBQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YF04V	Samples
TXS0104VDR	ACTIVE	SOIC	D	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TXS0104V	Samples
TXS0104VQBQARQ1	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YF04VQ	Samples
TXS0104VQRUTRQ1	ACTIVE	UQFN	RUT	12	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	1SW	Samples
TXS0104VRGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YF04V	Samples
TXS0104VRUTR	ACTIVE	UQFN	RUT	12	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	1SV	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



# PACKAGE OPTION ADDENDUM

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

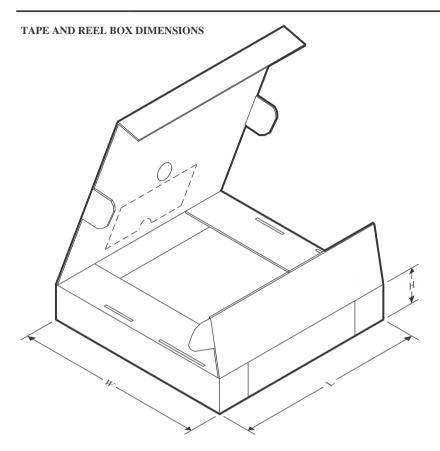


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TXS0104VBQAR	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1
TXS0104VDR	SOIC	D	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1
TXS0104VQBQARQ1	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1
TXS0104VQRUTRQ1	UQFN	RUT	12	3000	180.0	8.4	2.0	2.3	0.75	4.0	8.0	Q1
TXS0104VRGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1
TXS0104VRUTR	UQFN	RUT	12	3000	180.0	8.4	2.0	2.3	0.75	4.0	8.0	Q1



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## \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TXS0104VBQAR	WQFN	BQA	14	3000	210.0	185.0	35.0
TXS0104VDR	SOIC	D	14	3000	340.5	336.1	32.0
TXS0104VQBQARQ1	WQFN	BQA	14	3000	210.0	185.0	35.0
TXS0104VQRUTRQ1	UQFN	RUT	12	3000	210.0	185.0	35.0
TXS0104VRGYR	VQFN	RGY	14	3000	360.0	360.0	36.0
TXS0104VRUTR	UQFN	RUT	12	3000	210.0	185.0	35.0



SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.



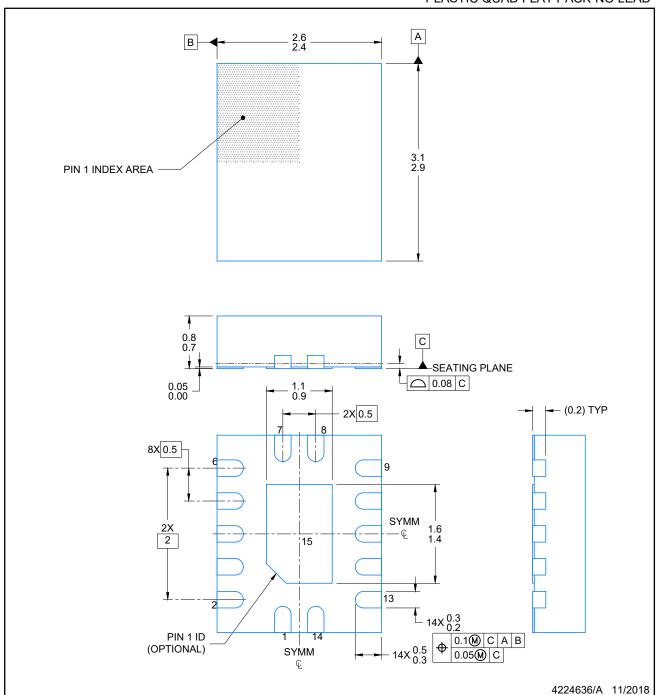
2.5 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



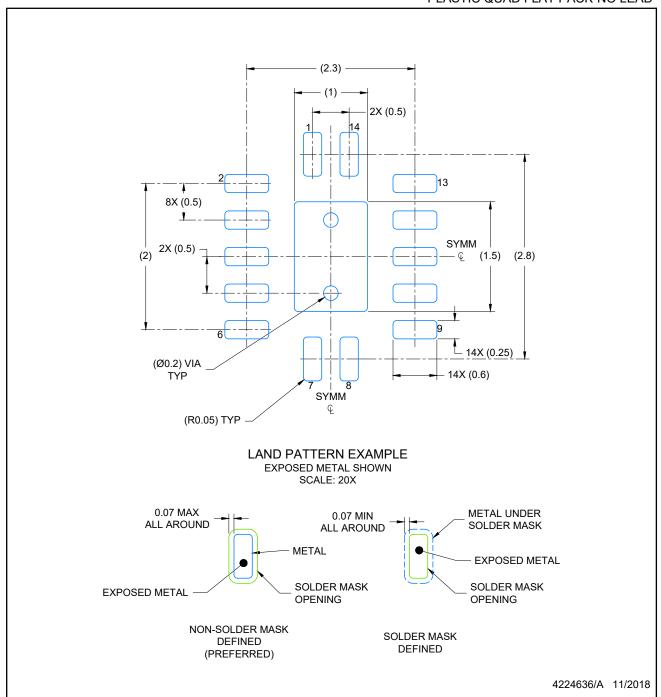
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#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

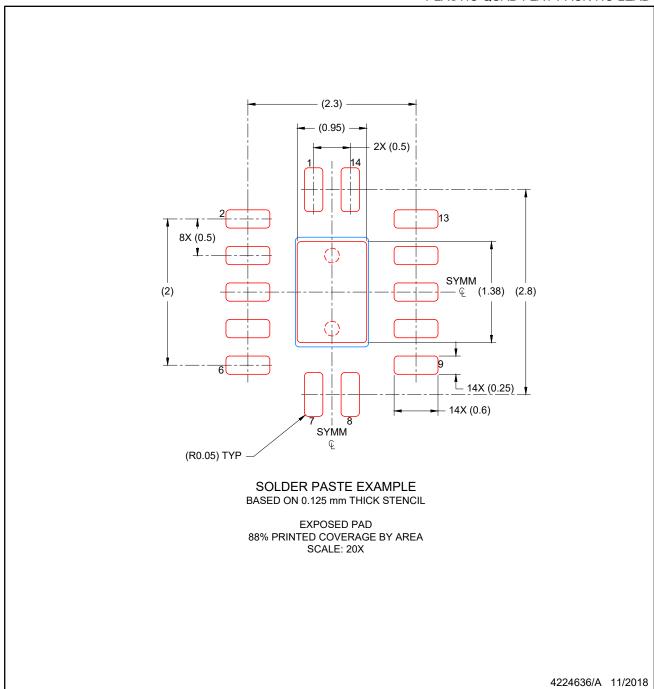




NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



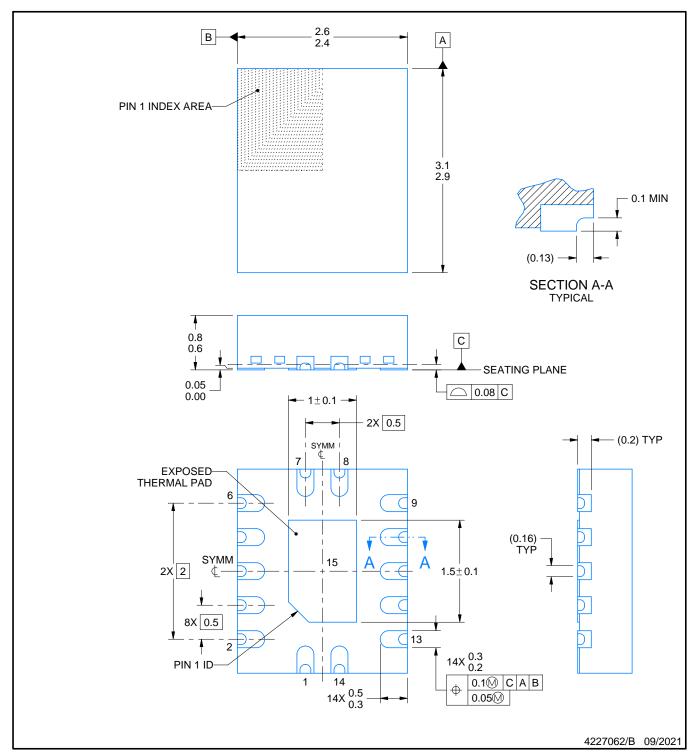


NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



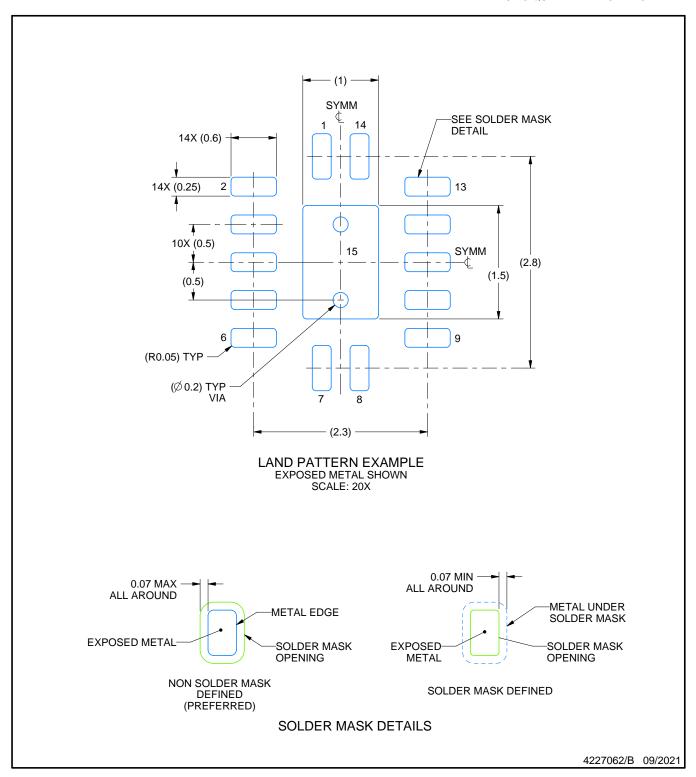




#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

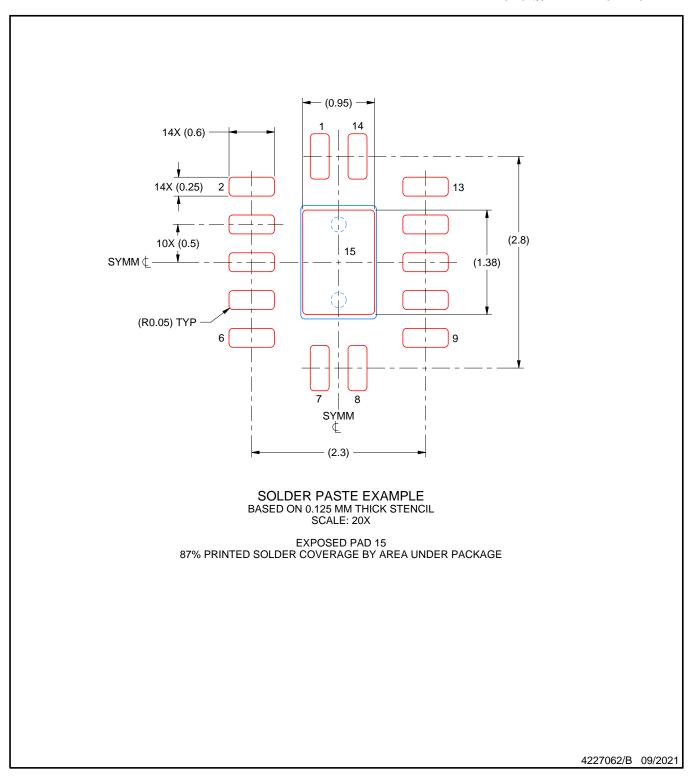




NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



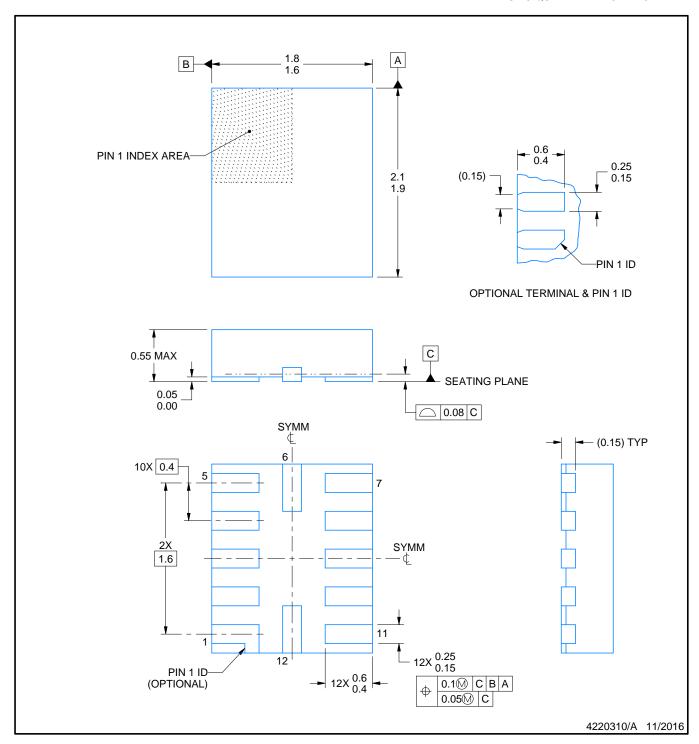


NOTES: (continued)

<sup>6.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



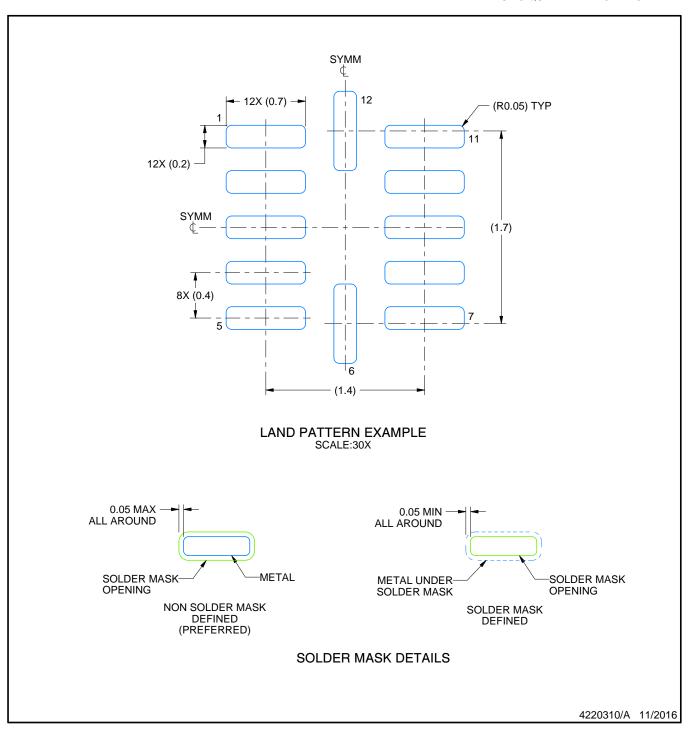




#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
   This drawing is subject to change without notice.

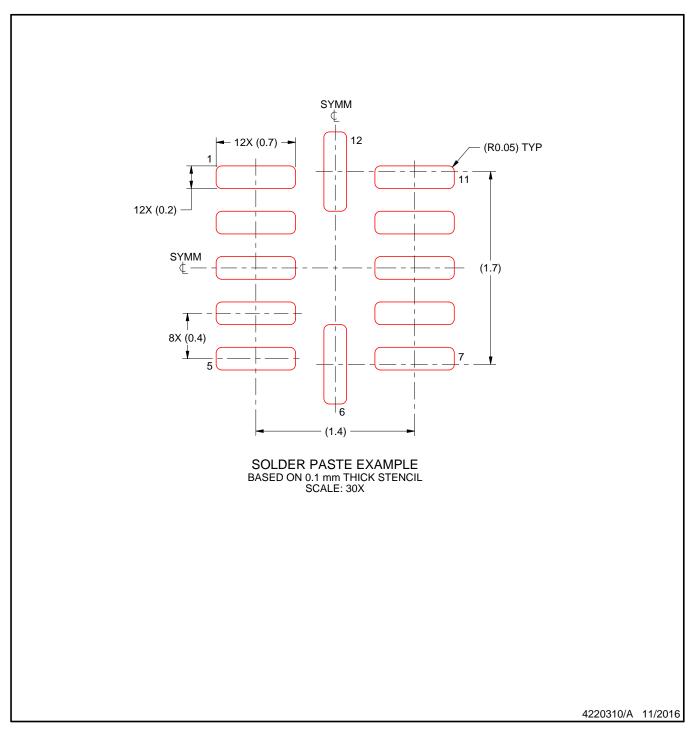




NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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